



# MCR100-8B

## 主要参数 MAIN CHARACTERISTICS

$I_{T(RMS)}$	1A
$V_{DRM}/V_{RRM}$	900V
$I_{GT}$	10-100 $\mu$ A

### 用途

- 半交流开关
- 相位控制

### 产品特性

- 玻璃钝化芯片，高可靠性和一致性
- 低通态电流和高浪涌电流能力
- 环保 RoHS 产品
- 芯片面积 1.36mm\*1.36mm（锯片后最小面积 1.30mm\*1.30mm）

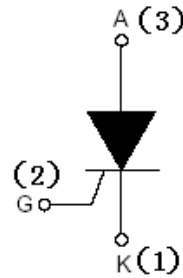
### APPLICATIONS

- Half AC switching
- Phase control

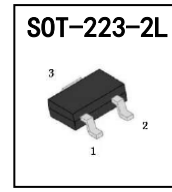
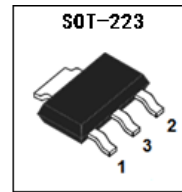
### FEATURES

- Glass-passivated mesa chip for high reliability and uniform
- Low on-state voltage and High  $I_{TSM}$
- RoHS products

## 封装 Package



序号 Pin	引线名称 Description
1	阴极 K
2	门极 G
3	阳极 A



## 订货信息 ORDER MESSAGES

有卤-编带	无卤-编带	有卤-袋装	印记 Marking	封装 Package
Halogen-Reel	Halogen-Free-Reel	Halogen-Bag		
MCR100-8B--NL-A	N/A	N/A	MCR100-8	SOT-223-2L
MCR100-8B-NC-A	N/A	N/A	MCR100-8	SOT-223

绝对最大额定值 ABSOLUTE RATINGS ( $T_C=25^\circ\text{C}$ )

项 目 Parameter	符 号 Symbol	试 验 条 件 Condition	数 值 Value	单 位 Unit
断态重复峰值电压 Repetitive peak off-state voltage	$V_{\text{DRM}}$		900	V
反向重复峰值电压 Repetitive peak reverse voltage	$V_{\text{RRM}}$		900	V
Non -Repetitive peak off-state voltage	$V_{\text{DSM}}$		950	V
Non -Repetitive peak reverse voltage	$V_{\text{RSM}}$		950	V
通态平均电流 Average on-state current	$I_{\text{T(AV)}}$		0.6	A
通态方均根电流 On-state RMS current	$I_{\text{T(RMS)}}$		1.0	A
非重复浪涌峰值通态电流 Non-repetitive surge peak on-state current	$I_{\text{TSM}}$	half sine cycle ( $t=10\text{ms}$ ), $T_j=25^\circ\text{C}$	12	A
熔断 $I^2t$ $I^2t$ for fusing	$I^2t$	half sine wave, $t=10\text{ms}$	0.72	$\text{A}^2\text{s}$
通态电流临界上升率 Repetitive rate of rise of on-state current after riggering	$dI/dt$	$I_{\text{TM}}=2.0\text{A}$ , $I_{\text{G}}=0.02\text{A}$ , $dI_{\text{G}}/dt=1.0\text{A}/\mu\text{s}$	50	$\text{A}/\mu\text{s}$
峰值门极电流 Peak gate current	$I_{\text{GM}}$	$t_p=20\mu\text{s}$ , $T_j=110^\circ\text{C}$	1	A
平均门极功率 Average gate power	$P_{\text{G(AV)}}$	$t_p=20\mu\text{s}$ , $T_j=110^\circ\text{C}$	0.1	W
存储温度 Storage temperature	$T_{\text{stg}}$		-40~150	$^\circ\text{C}$
操作结温 Operation junction temperature	$T_{\text{VJ}}$		-40~125	$^\circ\text{C}$



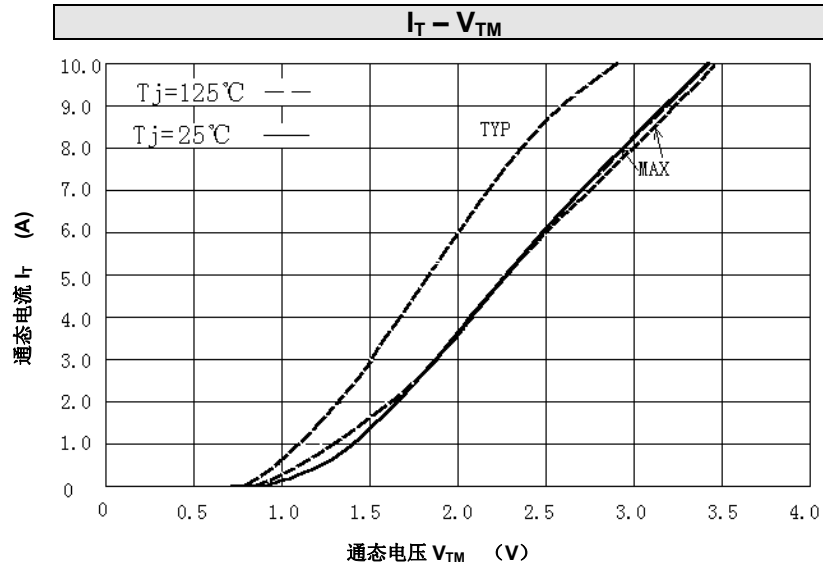
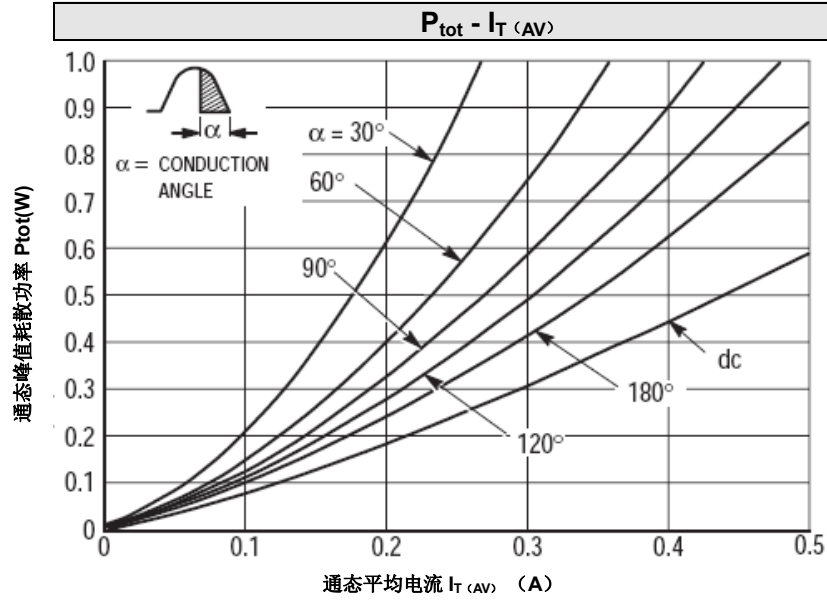
电特性 ELECTRICAL CHARACTERISTIC ( $T_c=25^\circ\text{C}$ )

项 目 Parameter	符 号 Symbol	测 试 条 件 Condition	最小 Min	典型 Typ	最大 Max	单位 Unit
断态峰值重复电流 Peak Repetitive Blocking Current	$I_{DRM}$	$V_{DM}=V_{DRM}, T_j=125^\circ\text{C}, R_{GK}=1\text{K}\Omega$	-	-	0.1	mA
反向峰值重复电流 Peak Repetitive Reverse Current	$I_{RRM}$	$V_{RM}=V_{RRM}, T_j=125^\circ\text{C}, R_{GK}=1\text{K}\Omega$	-	-	0.1	mA
峰值通态电压 Peak on-state voltage	$V_{TM}$	$I_{TM}=1\text{A}$	-	—	1.7	V
门极触发电流 Gate trigger current	$I_{GT}$	$V_{AK}=12\text{V}, R_L=33\Omega$	10	-	100	$\mu\text{A}$
门极触发电压 Gate trigger voltage	$V_{GT}$	$V_{AK}=12\text{V}, R_L=33\Omega$	-	0.6	0.8	V
维持电流 Holding current	$I_H$	$V_{AK}=12\text{V}, I_T=0.1\text{A}$	-	-	5	mA
擎住电流 Latch current	$I_L$	$V_{AK}=12\text{V}, I_T=0.1\text{A}$	-	-	5	mA
断态临界电压上升率 Rise of off- state voltage	dV/dt	$V_{DM}=2/3V_{DRM},$ $T_j=110^\circ\text{C}, R_{GK}=1\text{K}\Omega$	50	100		V/ $\mu\text{s}$



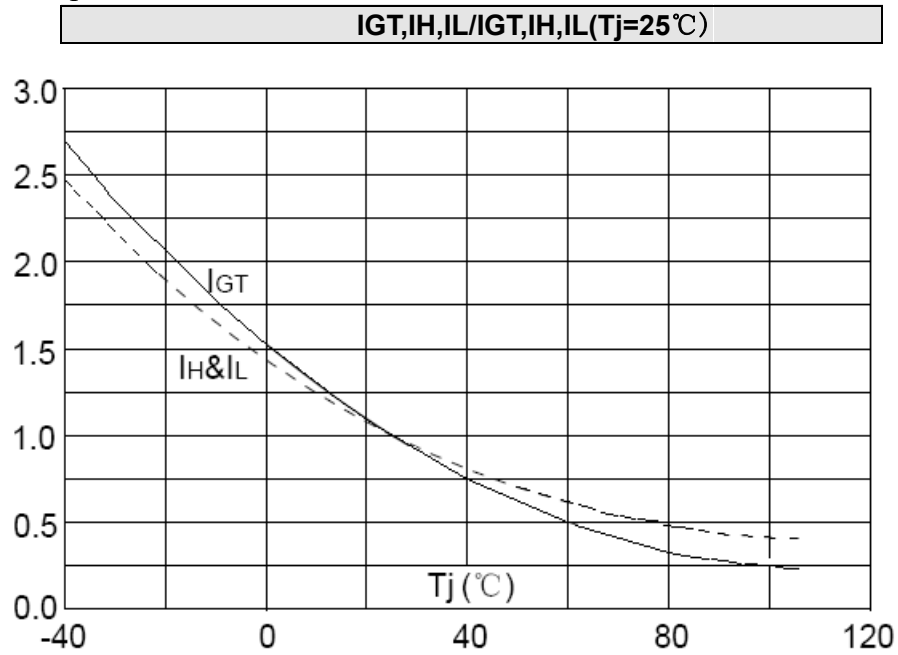


特征曲线 ELECTRICAL CHARACTERISTICS (curves)





Relative variations of gate trigger current, holding current and latching current versus junction temperature.

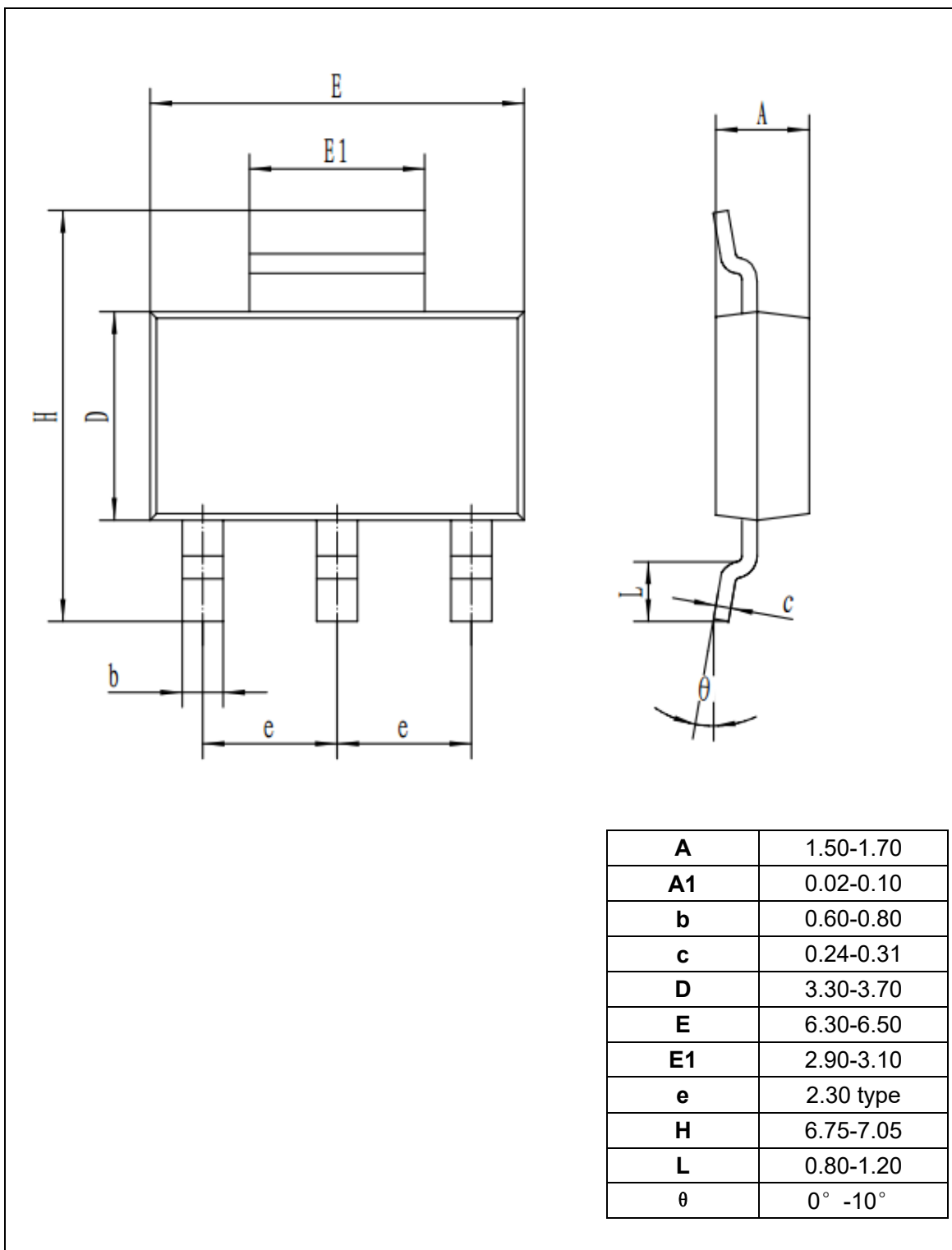




外形尺寸 PACKAGE MECHANICAL DATA

SOT-223

单位Unit : mm

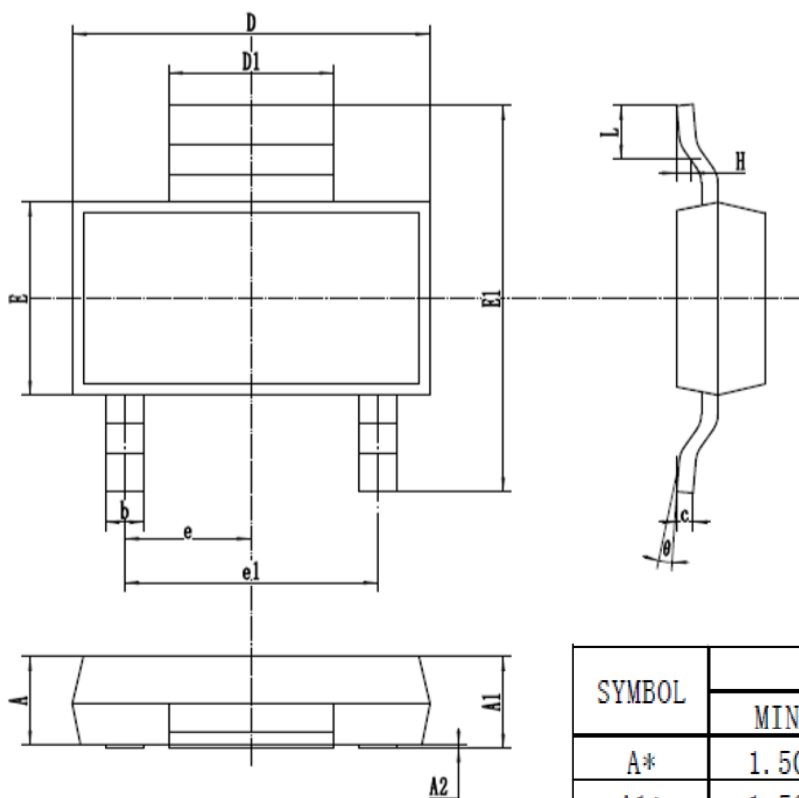




外形尺寸 PACKAGE MECHANICAL DATA

SOT-223-2L

单位 Unit : mm



SYMBOL	mm		
	MIN	NOR	MAX
A*	1.50	1.60	1.70
A1*	1.56	1.66	1.76
A2	0.02	-	0.10
b*	0.65	0.70	0.75
c*	0.25	0.30	0.35
D*	6.35	6.50	6.65
D1*	2.85	3.00	3.15
E*	3.35	3.50	3.65
E1*	6.85	7.00	7.15
e*	2.30 BASIC		
e1*	4.60 BASIC		
L*	0.75	0.95	1.15
H*	0.20	0.25	0.30
θ	-	-	10°

注：\*标注为检验项目。



### 注意事项

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3. 在电路设计时请不要超过器件的绝对最大额定值，否则会影响整机的可靠性。
4. 本说明书如有版本变更不另外告知。

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3. Please do not exceed the absolute maximum ratings of the device when circuit designing.
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